WHAT IS CLAIMED IS:

1. A magnetic random access memory comprising:

memory cells each including at least one tunneling magnetoresistive element which stores information by use of a tunneling magnetoresistive effect and a selection element which selects the tunneling magnetoresistive element, and

a read circuit which reads information from the tunneling magnetoresistive element by applying read voltage to the memory cell and causing a current to flow through the tunneling magnetoresistive element via the selection element,

wherein the read circuit includes a voltage setting section used to apply voltage which makes a resistance variation rate of the tunneling magnetoresistive element substantially equal to half a resistance variation rate thereof obtained when 0 V is applied across the tunneling magnetoresistive element to the tunneling magnetoresistive element at the information read time.

2. A magnetic random access memory according to claim 1, in which the memory cells are arranged in a matrix form and which further comprises word lines each connected to control electrodes of those of the selection elements of the memory cells which are arranged on a corresponding one of rows and bit lines each connected to one-side ends of those of the

tunneling magnetoresistive elements of the memory cells which are arranged on a corresponding one of columns, wherein the read circuit includes a current specifying section which specifies a current flowing through the memory cell, and a comparator section which compares potential corresponding to an intermediate value between "1" and "0" of storage information in the bit line with potential read from the memory cell to read the storage information.

3. A magnetic random access memory according to claim 1, wherein each of the memory cells includes a plurality of tunneling magnetoresistive elements and the other ends of the tunneling magnetoresistive elements of each memory cell are connected to one end of the current path of the selection element.

4. A magnetic random access memory according to claim 2, wherein the selection element is a MOSFET and the control electrode is a gate electrode thereof.

5. A magnetic random access memory according to claim 2, wherein the selection element is a bipolar transistor and the control electrode is a base electrode thereof.

6. A magnetic random access memory according to claim 1, in which the selection element is a diode and the memory cells are arranged in a matrix form and which further comprises word lines each connected to cathodes of those of the diodes which are arranged on a

corresponding one of rows and bit lines each connected to one-side ends of those of the tunneling magnetoresistive elements of the memory cells which are arranged on a corresponding one of columns, wherein the read circuit includes a current specifying section which specifies a current flowing through the memory cell, and a comparator section which compares potential corresponding to an intermediate value between "1" and "0" of storage information in the bit line with potential read from the memory cell to read the storage information.

7. A magnetic random access memory according to claim 6, wherein each of the memory cells includes a plurality of tunneling magnetoresistive elements and the other ends of the tunneling magnetoresistive elements of each memory cell are connected to an anode of the diode.

8. A magnetic random access memory according to claim 3, wherein at least two of the plurality of tunneling magnetoresistive elements connected to the selection element are connected in parallel.

9. A magnetic random access memory according to claim 3, wherein at least two of the plurality of tunneling magnetoresistive elements connected to the selection elements are connected in series.

10. A magnetic random access memory comprising:

memory cells each including at least one tunneling

magnetoresistive element which stores information by use of a tunneling magnetoresistive effect and a selection element which selects the tunneling magnetoresistive element, and

a read circuit which reads information from the tunneling magnetoresistive element by applying read voltage to the memory cell and causing a current to flow through the tunneling magnetoresistive element via the selection element,

wherein the read circuit includes a voltage setting section used to apply voltage which is higher than the voltage applied to the tunneling magnetoresistive element by at least a voltage drop occurring across the selection element to the tunneling magnetoresistive element at the information read time.

11. A magnetic random access memory according to claim 10, in which the memory cells are arranged in a matrix form and which further comprises word lines each connected to control gates of those of the selection elements of the memory cells which are arranged on a corresponding one of rows and bit lines each connected to one-side ends of the tunneling magnetoresistive elements of the memory cells which are arranged on corresponding one of columns, wherein the read circuit includes a current specifying section which specifies a current flowing through the memory cell, and a comparator section which compares potential

corresponding to an intermediate value between "1" and "0" of storage information in the bit line with potential read from the memory cell to read the storage information.

12. A magnetic random access memory according to claim 10, wherein each of the memory cells includes a plurality of tunneling magnetoresistive elements and the other ends of the tunneling magnetoresistive elements of each memory cell are connected to one end of the current path of the selection element.

13. A magnetic random access memory according to claim 11, wherein the selection element is a MOSFET and the control electrode is a gate electrode thereof.

14. A magnetic random access memory according to claim 11, wherein the selection element is a bipolar transistor and the control electrode is a base electrode thereof.

15. A magnetic random access memory according to claim 10, in which the selection element is a diode and the memory cells are arranged in a matrix form and which further comprises word lines each connected to cathodes of those of the diodes which are arranged on a corresponding one of rows and bit lines each connected to one-side ends of those of the tunneling magneto-resistive elements of the memory cells which are arranged on a corresponding one of columns, wherein the read circuit includes a current specifying section

which specifies a current flowing through the memory cell, and a comparator section which compares potential corresponding to an intermediate value between "1" and "0" of storage information in the bit line with potential read from the memory cell to read the storage information.

16. A magnetic random access memory according to claim 15, wherein each of the memory cells includes a plurality of tunneling magnetoresistive elements and the other ends of the tunneling magnetoresistive elements of each memory cell are connected to an anode of the diode.

17. A magnetic random access memory according to claim 12, wherein at least two of the plurality of tunneling magnetoresistive elements connected to the selection elements are connected in parallel.

18. A magnetic random access memory according to claim 12, wherein at least two of the plurality of tunneling magnetoresistive elements connected to the selection element are connected in series.

19. A magnetic random access memory comprising:

tunneling magnetoresistive elements which store information by use of a tunneling magnetoresistive effect,

bit lines connected to one-side ends of the tunneling magnetoresistive elements,

word lines connected to the other ends of the

tunneling magnetoresistive elements, and

a read circuit which reads information from the tunneling magnetoresistive element by applying read voltage to the tunneling magnetoresistive elements and causing a current to flow through the tunneling magnetoresistive element,

wherein the read circuit includes a voltage setting section used to apply voltage which makes a resistance variation rate of the tunneling magnetoresistive element substantially equal to half a resistance variation rate thereof obtained when 0 V is applied across the tunneling magnetoresistive element to the tunneling magnetoresistive element at the information read time.

20. A magnetic random access memory according to claim 19, wherein the tunneling magnetoresistive elements are arranged in a matrix form and the read circuit includes a current specifying section which specifies a current flowing through the tunneling magnetoresistive element and a comparator section which compares potential corresponding to an intermediate value between "1" and "0" of storage information in the bit line with potential read from the tunneling magnetoresistive element to read the storage information.

21. A magnetic random access memory according to claim 20, wherein the bit lines are arranged above the

tunneling magnetoresistive elements.

22. A magnetic random access memory according to claim 21, wherein the bit lines are arranged below the tunneling magnetoresistive elements.

23. A magnetic random access memory according to claim 20, wherein the word lines are arranged above the tunneling magnetoresistive elements.

24. A magnetic random access memory according to claim 20, wherein the word lines are arranged below the tunneling magnetoresistive elements.